

TOSHIBA IGBT Module Silicon N Channel IGBT

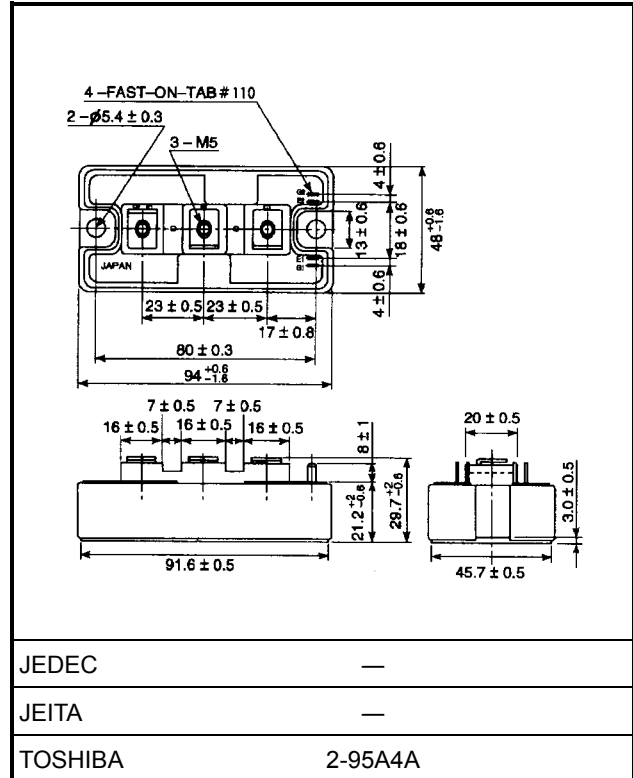
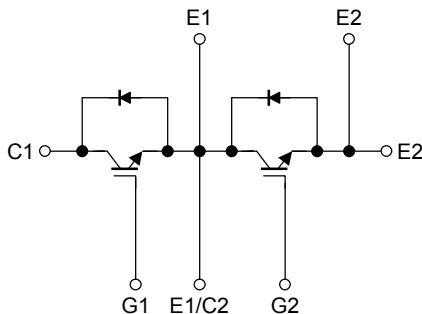
# MG100Q2YS65H

High Power & High Speed Switching Applications

Unit: mm

- High input impedance
- Enhancement-mode
- The electrodes are isolated from case.

## Equivalent Circuit



Weight: 255 g (typ.)

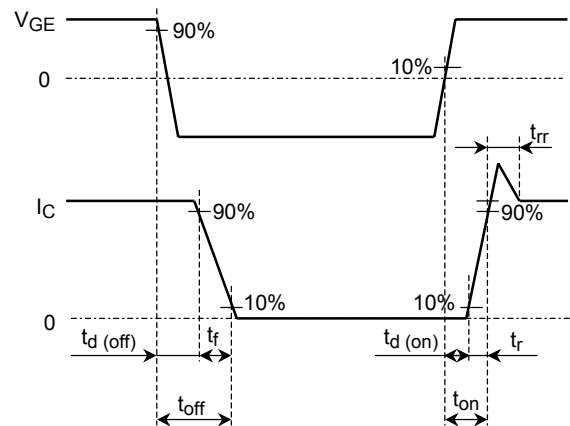
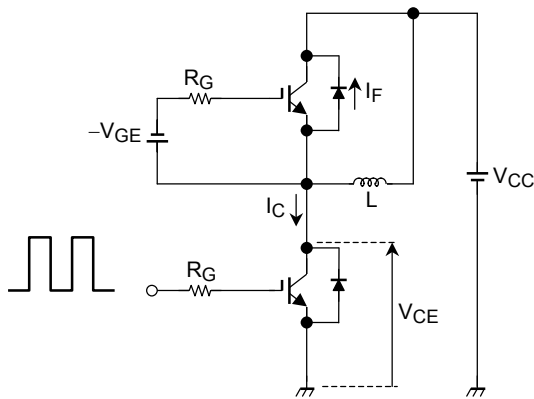
## Maximum Ratings (Ta = 25°C)

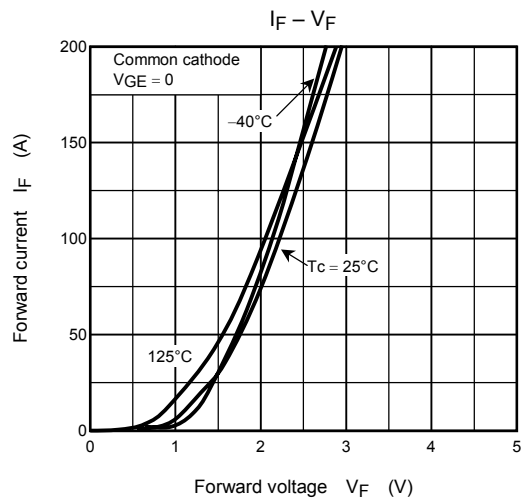
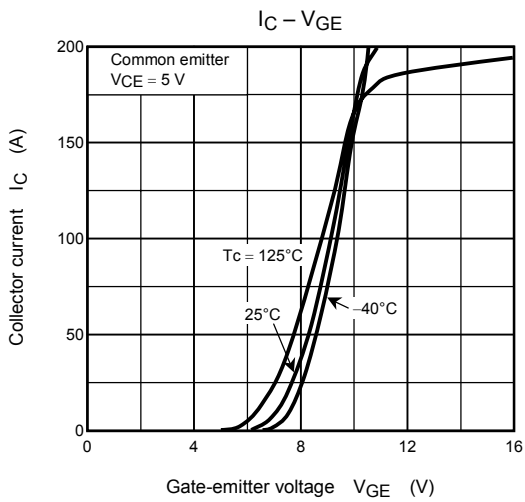
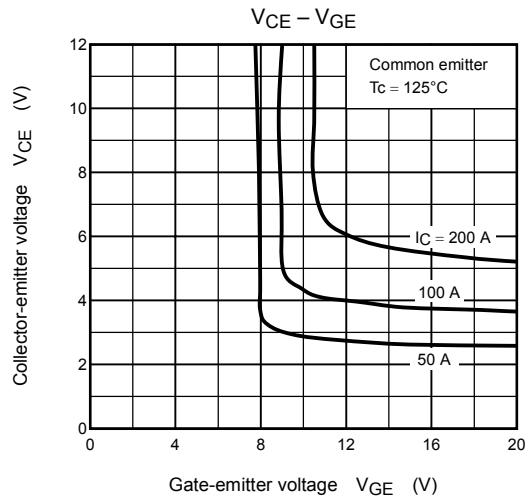
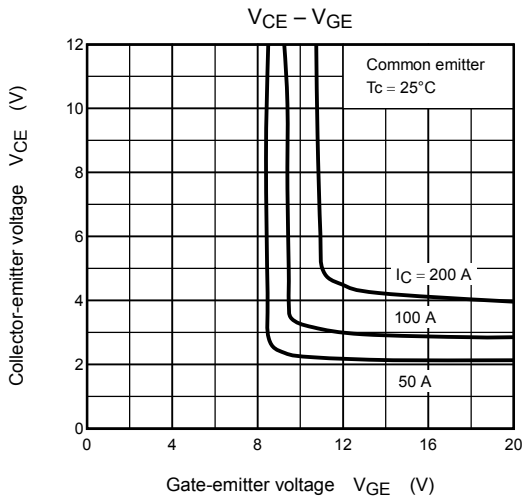
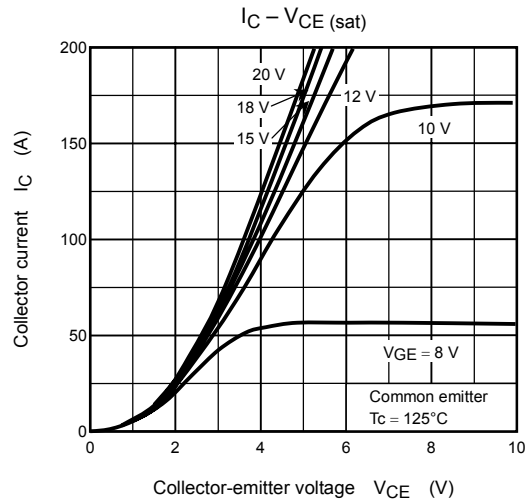
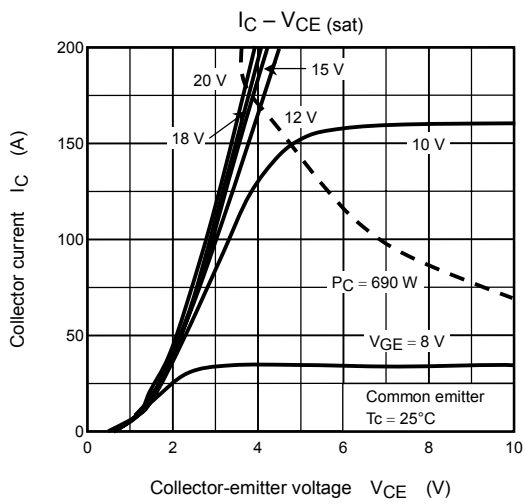
Characteristics	Symbol	Rating	Unit
Collector-emitter voltage	V <sub>CES</sub>	1200	V
Gate-emitter voltage	V <sub>GES</sub>	±20	V
Collector current	DC	I <sub>C</sub>	100
	1 ms	I <sub>CP</sub>	200
Forward current	DC	I <sub>F</sub>	100
	1 ms	I <sub>FM</sub>	200
Collector power dissipation (T <sub>c</sub> = 25°C)	P <sub>C</sub>	690	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-40 to 125	°C
Isolation voltage	V <sub>Isol</sub>	2500 (AC 1 minute)	V
Screw torque	Terminal	—	3
	Mounting	—	3
			N•m

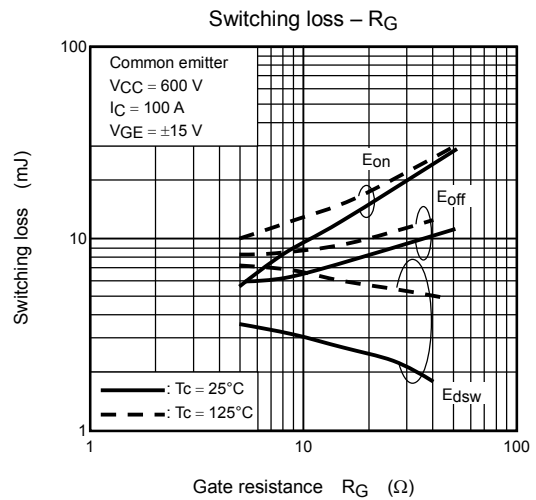
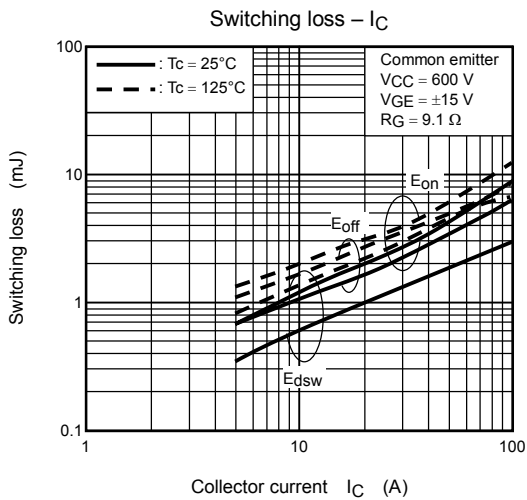
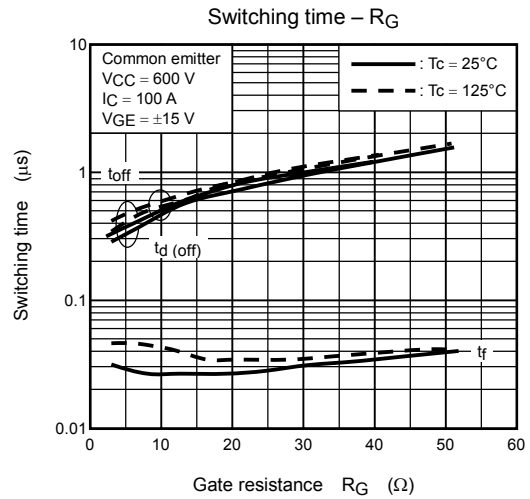
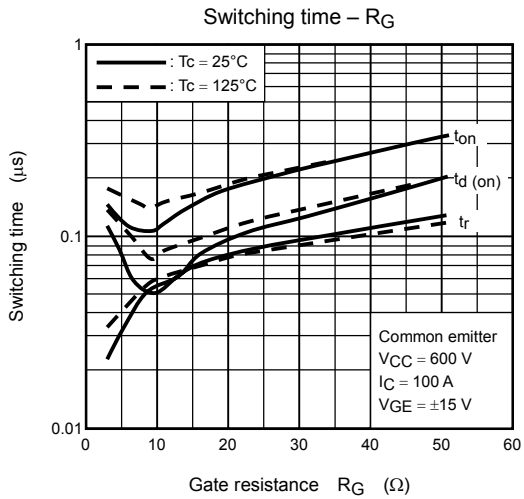
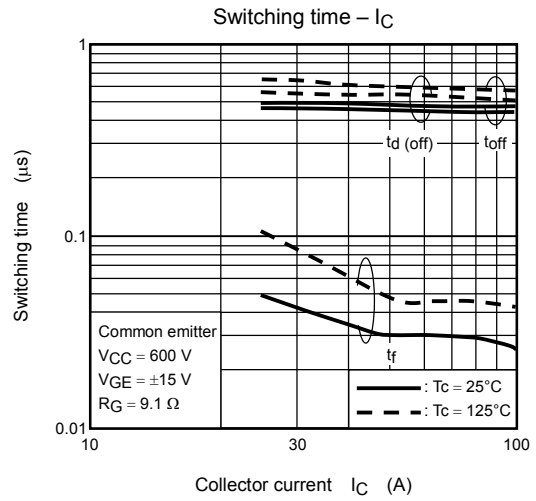
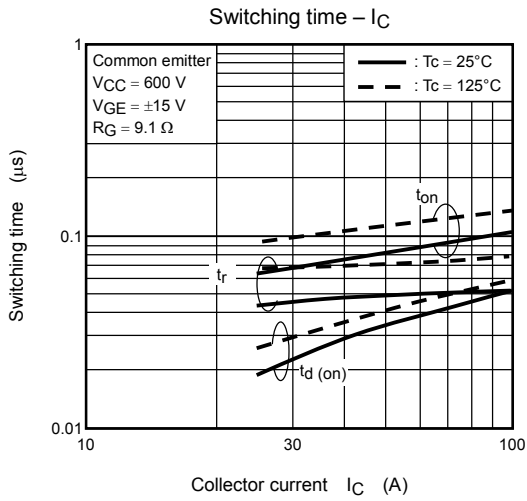
## Electrical Characteristics (Ta = 25°C)

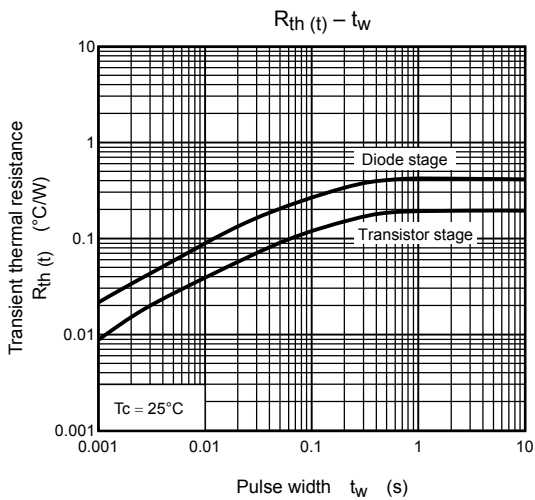
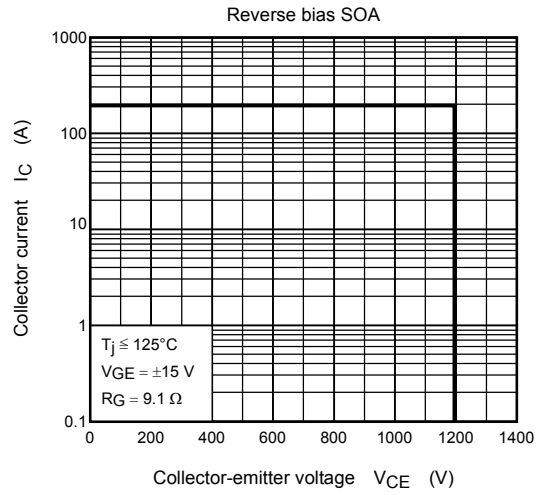
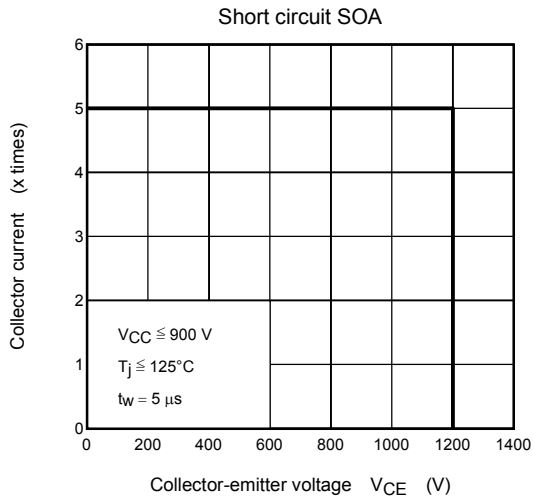
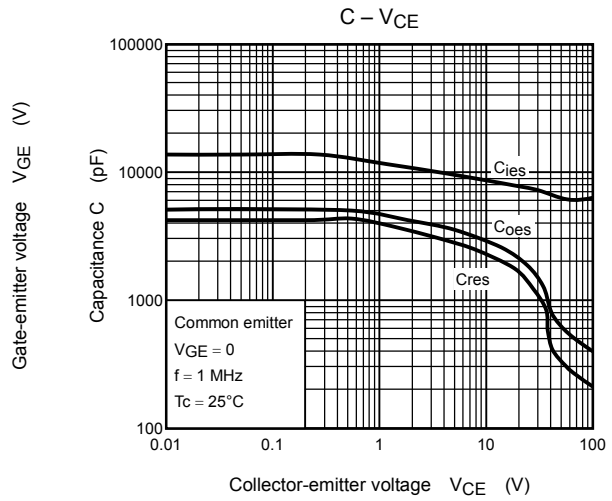
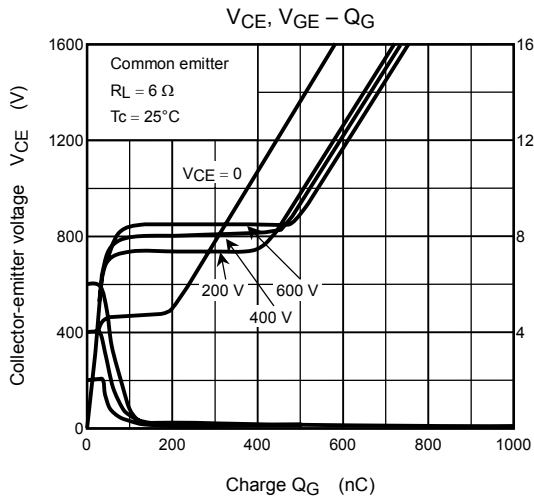
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current		$I_{GES}$	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$	—	—	$\pm 500$	nA	
Collector cut-off current		$I_{CES}$	$V_{CE} = 1200 \text{ V}, V_{GE} = 0$	—	—	2.0	mA	
Gate-emitter cut-off voltage		$V_{GE (off)}$	$I_C = 100 \text{ mA}, V_{CE} = 5 \text{ V}$	4.0	—	7.0	V	
Collector-emitter saturation voltage		$V_{CE (sat)}$	$I_C = 100 \text{ A}, V_{GE} = 15 \text{ V}$	$T_C = 25^\circ\text{C}$	—	3.0	4.0	V
				$T_C = 125^\circ\text{C}$	—	3.6	—	
Input capacitance		$C_{ies}$	$V_{CE} = 10 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$	—	8500	—	pF	
Switching time	Turn-on delay time	$t_{d (on)}$	Inductive load $V_{CC} = 600 \text{ V}, I_C = 100 \text{ A}$ $V_{GE} = \pm 15 \text{ V}, R_G = 9.1 \Omega$	—	0.05	—	$\mu\text{s}$	
	Rise time	$t_r$		—	0.05	—		
	Turn-on time	$t_{on}$		—	0.10	—		
	Turn-off delay time	$t_{d (off)}$		—	0.55	—		
	Fall time	$t_f$		—	0.05	0.15		
	Turn-off time	$t_{off}$		—	0.60	—		
Forward voltage		$V_F$	$I_F = 100 \text{ A}, V_{GE} = 0$	—	2.4	3.5	V	
Reverse recovery time		$t_{rr}$	$I_F = 100 \text{ A}, V_{GE} = -10 \text{ V}, di/dt = 700 \text{ A}/\mu\text{s}$	—	0.1	—	$\mu\text{s}$	
Thermal resistance		$R_{th (j-c)}$	Transistor stage	—	—	0.18	$^\circ\text{C}/\text{W}$	
			Diode stage	—	—	0.41		
Switching loss	Turn-on	$E_{on}$	Inductive load $V_{CC} = 600 \text{ V}, I_C = 100 \text{ A}$ $V_{GE} = \pm 15 \text{ V}, R_G = 9.1 \Omega$ $T_C = 125^\circ\text{C}$	—	10	—	mJ	
	Turn-off	$E_{off}$		—	8	—		

Note: Switching time measurement circuit and input/output waveforms









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